

Electronic Supplementary Information

Mass Production of SiC/SiO_x Nanochain Heterojunctions with High Purities

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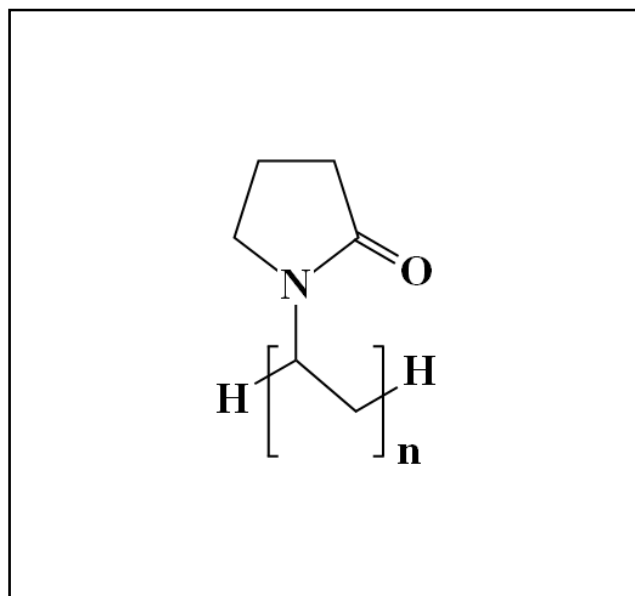


Figure S1. Molecular structures of PVP.

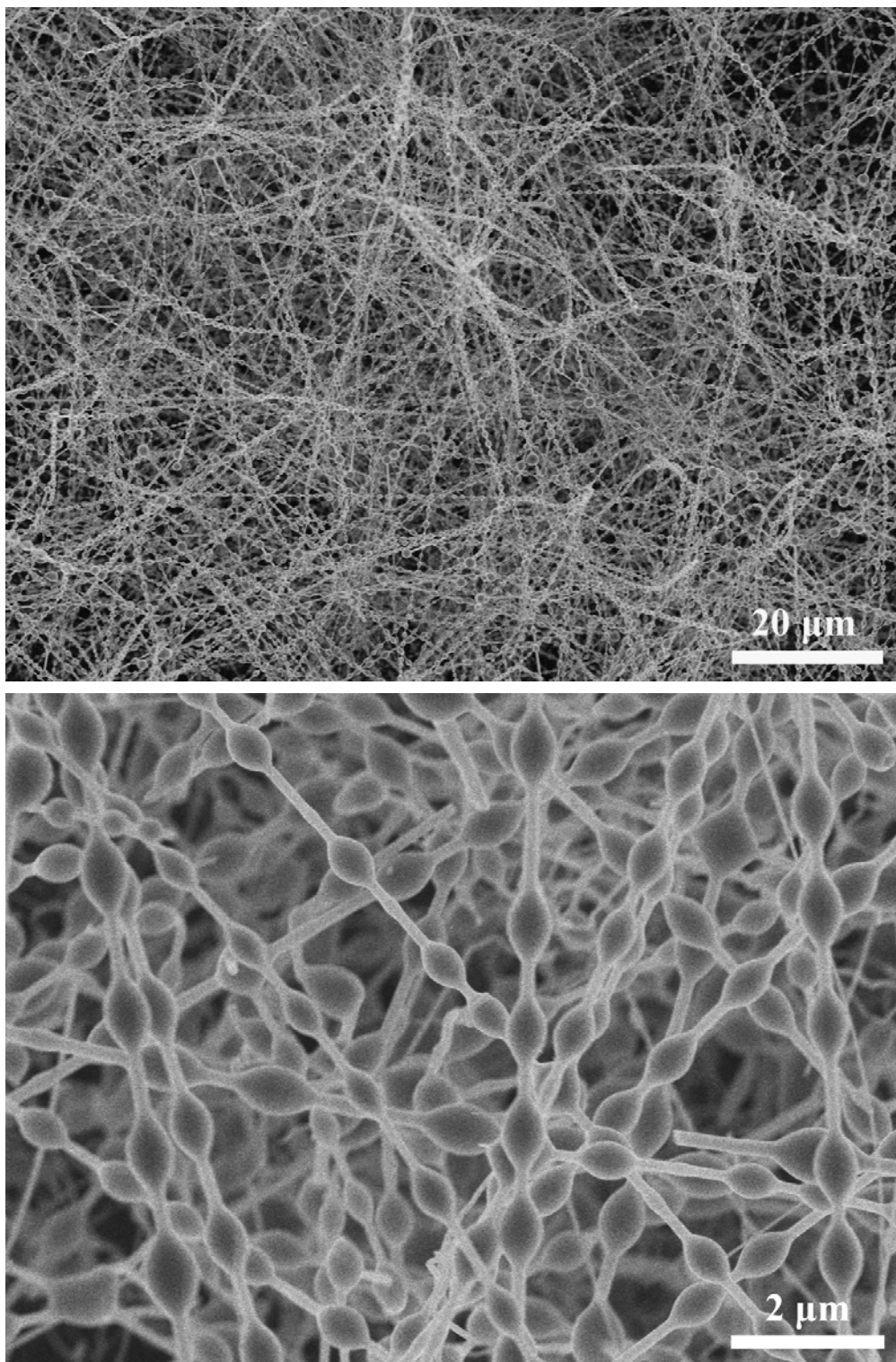


Figure S3. Typical SEM images of the resultant nanostructures of Sample C under different magnifications.

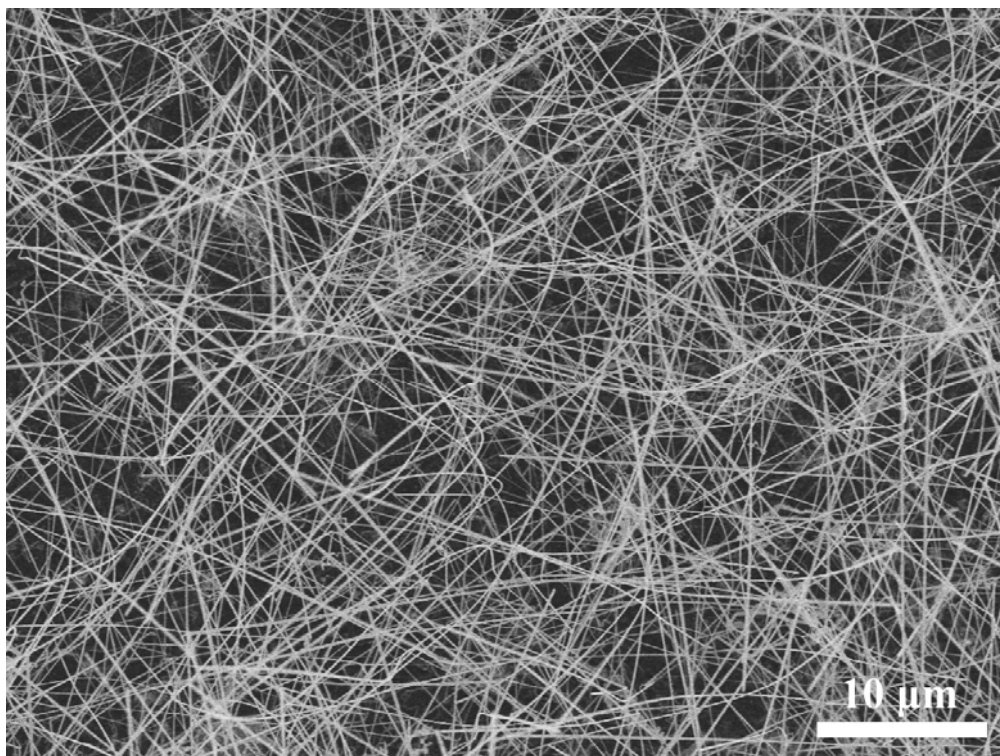


Figure S4. A typical SEM image of the resultant nanostructures of Sample A under a low magnification.

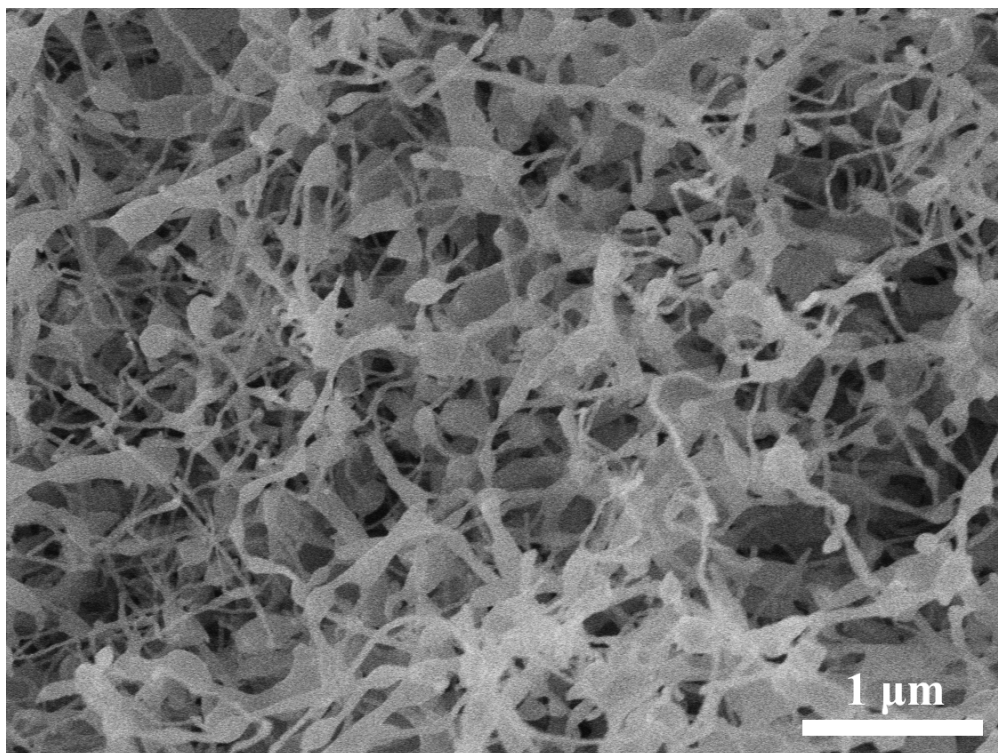


Figure S5. A typical SEM image of the resultant nanostructures of Sample B under a low magnification.

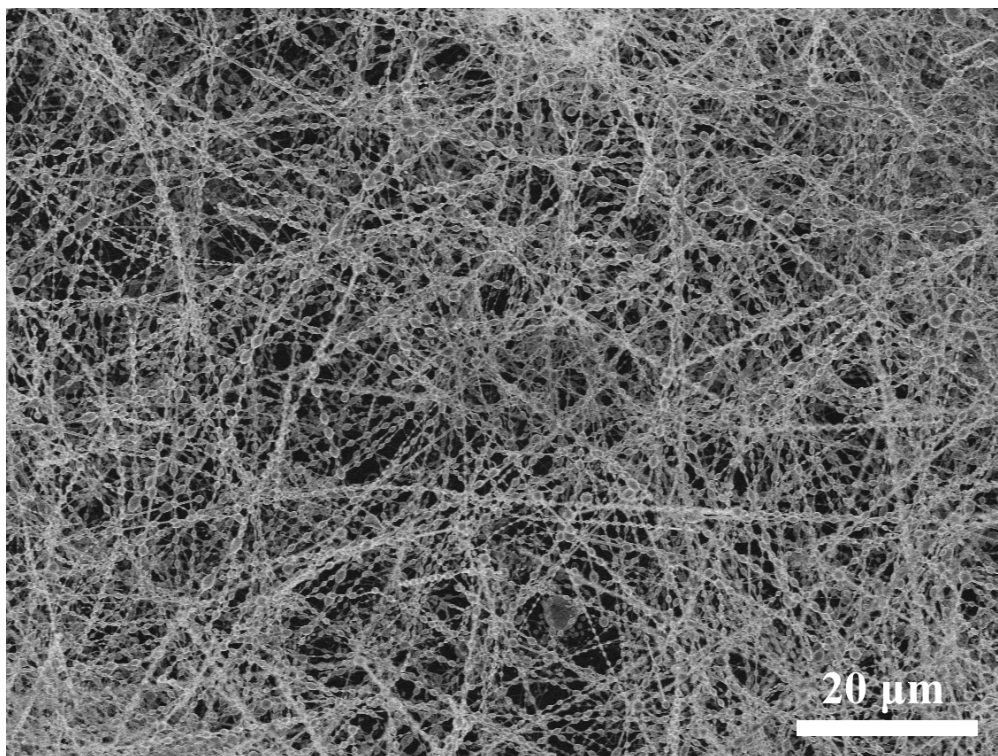


Figure S6. A representative SEM image of the resultant nanostructures of Sample D under a low magnification.

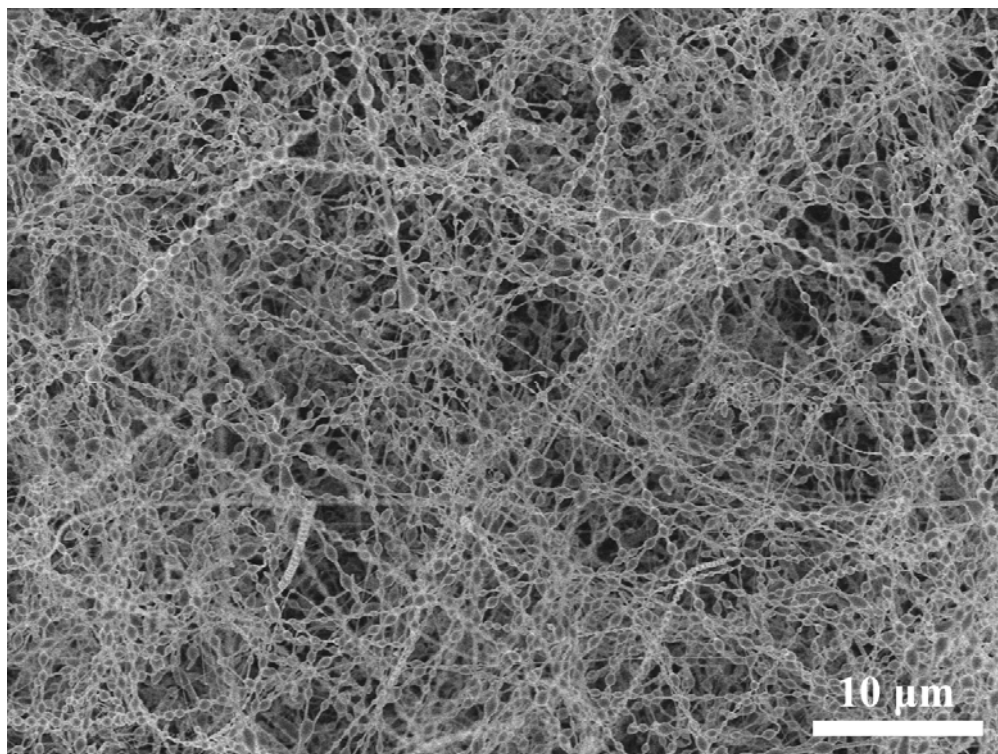


Figure S7. A representative SEM image of the resultant nanostructures of Sample E under a low magnification.